

Attorney Docket No.: 39611.2

DAU 2814
9/a
J Brown
11/30/98

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Byung-Chul AHN et al.

Serial No.: 08/918,119

Filed: August 27, 1997

For: THIN FILM TRANSISTOR AND METHOD OF MAKING SAME



Date: November 17, 1998

Group Art Unit: 2814

Examiner: N. NGO

Assistant Commissioner for Patents
Washington, D.C. 20231

AMENDMENT

Sir:

In response to the Office Action issued on August 20, 1998, please ~~consider~~ **RECEIVED**
the above-identified patent application amended as follows:

NOV 25 1998

IN THE CLAIMS:

GROUP 2100

Please amend the claims as follows:

1. (Amended) A thin film transistor comprising:

a substrate; and

a gate including a double-layered structure having a first metal layer which is a bottom layer disposed on the substrate and a second metal layer disposed on the [substrate] first metal layer, the first metal layer including aluminum, the second metal layer being arranged on the first metal layer to prevent hillock at the sides of the aluminum first metal layer, the first metal layer being wider than the second metal layer by about 1 to 4 μ m.